

November 2013

FDP020N06B — N-Channel PowerTrench[®] MOSFET

FDP020N06B N-Channel PowerTrench[®] MOSFET $60 V, 313 A, 2 m\Omega$

Features

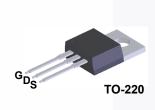
- $R_{DS(on)}$ = 1.65 m Ω (Typ.) @ V_{GS} = 10 V, I_D = 100 A
- Low FOM R_{DS(on)} * Q_G
- Low Reverse-Recovery Charge, Q_{rr} = 194 nC
- Soft Reverse-Recovery Body Diode
- Enables High Efficiency in Synchronous Rectification
- Fast Switching Speed
- 100% UIL Tested
- RoHS Compliant

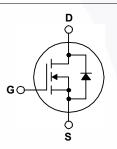
Description

This N-Channel MOSFET is produced using Fairchild Semiconductor's advanced PowerTrench[®] process that has been tailored to minimize the on-state resistance while maintaining superior switching performance.

Applications

- Synchronous Rectification for ATX / Server / Telecom PSU
- Battery Protection Circuit
- Motor Drives and Uninterruptible Power Supplies
- Renewable System





Absolute Maximum Ratings T_C = 25°C unless otherwise noteed.

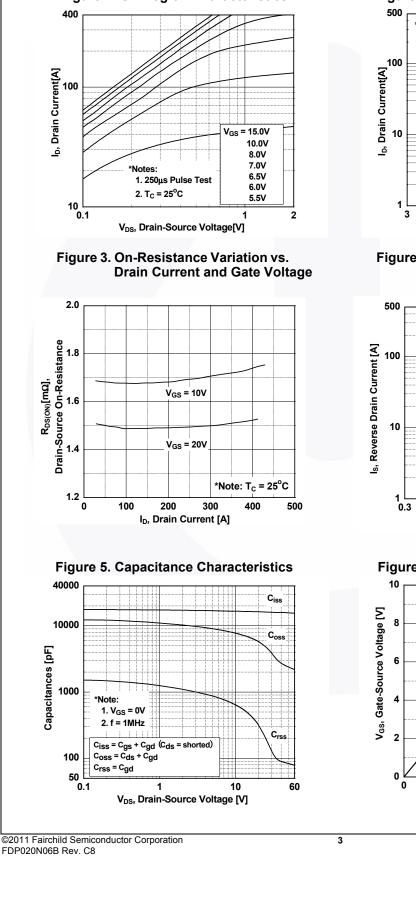
Symbol		FDP020N06B_F102	Unit		
V _{DSS}	Drain to Source Voltage	60	V		
V _{GSS}	Gate to Source Voltage		±20	V	
I _D		- Continuous (T _C = 25 ^o C, Silicon Limited)	313*		
	Drain Current	- Continuous (T _C = 100 ^o C, Silicon Limited)	221*	Α	
		- Continuous (T _C = 25 ^o C, Package Limited)	120	1	
I _{DM}	Drain Current	- Pulsed (Note 1)	1252	Α	
E _{AS}	Single Pulsed Avalanche	1859	mJ		
dv/dt	Peak Diode Recovery dv/	6.0	V/ns		
P _D	Power Dissipation	(T _C = 25°C)	333	W	
	Power Dissipation	- Derate Above 25°C	2.2	W/ºC	
T _J , T _{STG}	Operating and Storage Te	-55 to +175	°C		
ΤL	Maximum Lead Temperature for Soldering, 1/8" from Case for 5 Seconds		300	°C	

* Package limitation current is 120A.

Thermal Characteristics

Symbol	Parameter	FDP020N06B_F102	Unit
$R_{ extsf{ heta}JC}$	Thermal Resistance, Junction to Case, Max.	0.45	°C/W
$R_{ hetaJA}$	Thermal Resistance, Junction to Ambient, Max.	62.5	0,00

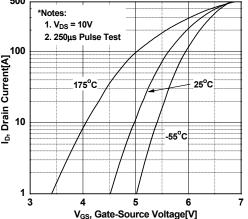
	Part Number Top Mark Packa		Package	e Packing Method Reel Size		Тар	e Width	Qua	ntity
		TO-220	Tube	N/A		N/A	50 units		
Electrical	Chara	acteristics T _c =	= 25°C unless	otherwise noted.					
Symbol	Parameter			Test Conditions		Min.	Тур.	Max.	Unit
Off Charact	eristics	5							
BV _{DSS}	Drain to Source Breakdown Voltage		/oltage	I _D = 250 μA, V _{GS} = 0 V		60	-	-	V
ΔBV _{DSS} / ΔT _J	Breakdown Voltage Temperature Coefficient		ure	$I_D = 250 \ \mu$ A, Referenced to 25° C		-	0.03	-	V/ºC
	Zero Gate Voltage Drain Current		ont	$V_{DS} = 48 V, V_{GS} = 0 V$ $V_{DS} = 48 V, T_{C} = 150^{\circ}C$		-	-	1	μA
DSS			ent			-	-	500	
GSS	Gate to Body Leakage Current		nt	V_{GS} = ±20 V, V_{DS} = 0	V	-	-	±100	nA
On Charact	eristics	5							
V _{GS(th)}	Gate Th	reshold Voltage		V _{GS} = V _{DS} , I _D = 250 μA		2.5	3.3	4.5	V
R _{DS(on)}	Static Dr	ain to Source On Res	sistance	V _{GS} = 10 V, I _D = 100		-	1.65	2.0	mΩ
9 _{FS}	Forward Transconductance			V _{DS} = 10 V, I _D = 100 A		-	263	-	S
Dynamic Cl	haracte	ristics							
C _{iss}	Input Capacitance					-	16100	20930	pF
C _{oss}		Capacitance		V _{DS} = 30 V, V _{GS} = 0 V, f = 1 MHz		-	3840	4992	pF
C _{rss}		Transfer Capacitance	e			-	127	-	pF
C _{oss(er)}	Energy Related Output Capacitance			V _{DS} = 30 V, V _{GS} = 0 V	-	5897	-	pF	
Q _{g(tot)}	0,	te Charge at 10V		$V_{DS} = 30 \text{ V}, \text{ I}_{D} = 100 \text{ A},$ $V_{GS} = 10 \text{ V}$ (Note 4)		-	206	268	nC
Q _{gs}	Gate to S	Source Gate Charge				-	87	-	nC
Q _{gs2}		Threshold to Plateau				-	36	-	nC
Q _{gd}	Gate to [Drain "Miller" Charge				-	34	-	nC
EŠR	Equivalent Series Resistance(G-S)		(G-S)	f = 1 MHz		-	0.9	-	Ω
Switching C	Charact	eristics							
t _{d(on)}	-	Delay Time					74	158	ns
t _r		Rise Time		$V_{DD} = 30 \text{ V}, \text{ I}_{D} = 100 \text{ A},$ $V_{GS} = 10 \text{ V}, \text{ R}_{G} = 4.7 \Omega$ (Note 4)		-	62	134	ns
t _{d(off)}		Delay Time				-	112	234	ns
t _f	Turn-Off	Fall Time				7 -	42	94	ns
)rain-Sour	ce Diod	e Characteristic	`e						
		n Continuous Drain to		de Forward Current		_	_	313*	А
	Maximun	n Pulsed Drain to Sou	urce Diode Fo			-	-	1252	Α
V _{SD}	Drain to Source Diode Forward Voltage		V _{GS} = 0 V, I _{SD} = 100 A		-	-	1.25	V	
t _{rr}	Reverse	se Recovery Time		$V_{GS} = 0 V, V_{DD} = 30 V, I_{SD} = 100 A,$		-	106	-	ns
Q _{rr}	Reverse Recovery Charge			$dI_{F}/dt = 100 \text{ A}/\mu \text{s}$		-	194	-	nC



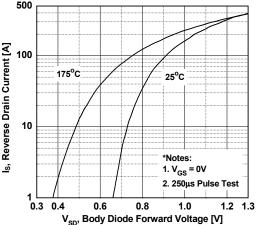
Typical Performance Characteristics

Figure 1. On-Region Characteristics

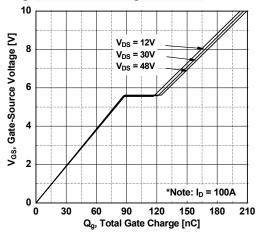
Figure 2. Transfer Characteristics



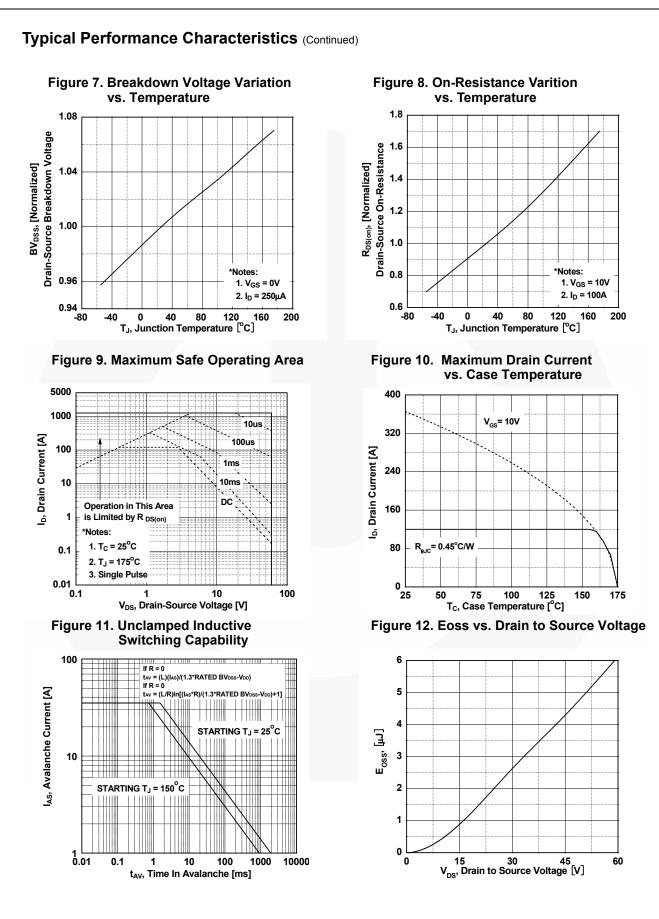








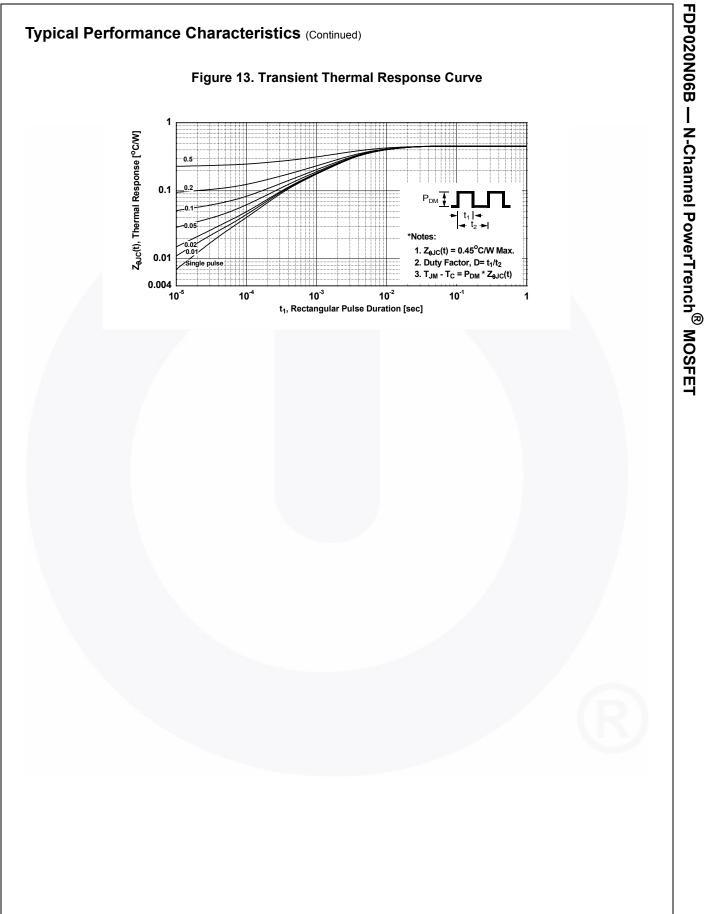
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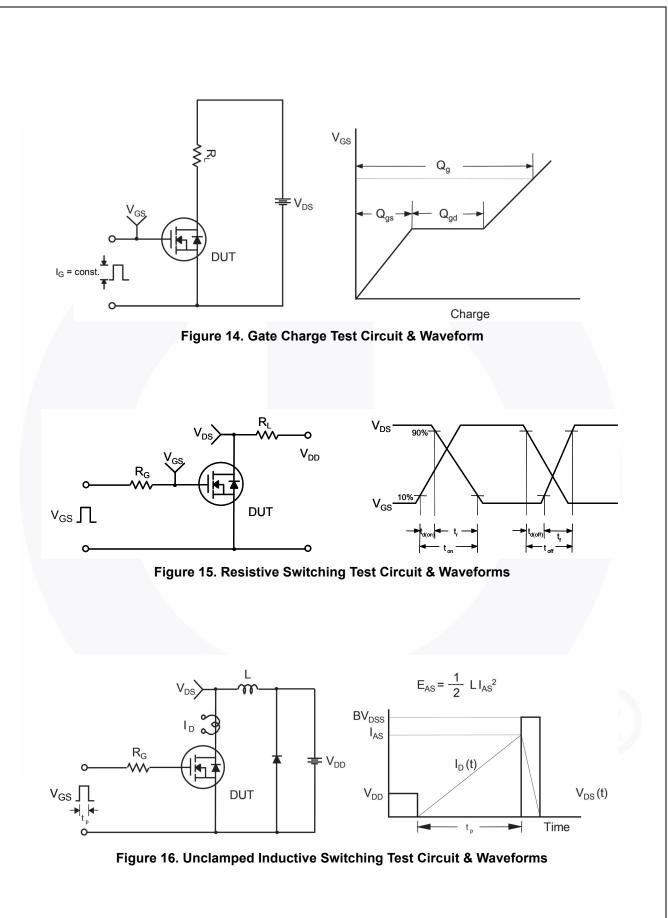


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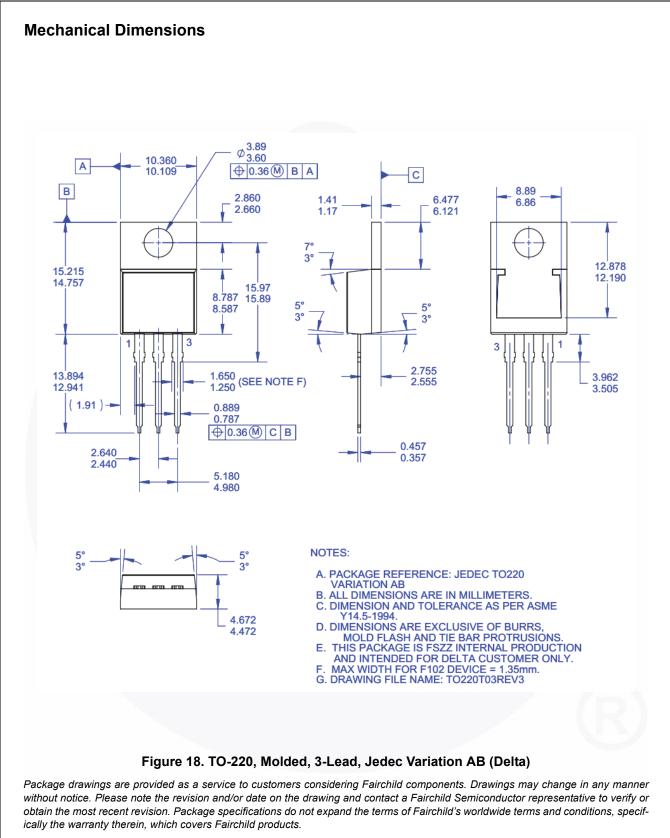
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DUT + v_{DS} a ۱_{SD} م L Driver R_G, Same Type as DUT L F ∨_{DD} $\prod V_{GS}$ • dv/dt controlled by R_{G} • I_{SD} controlled by pulse period Î Gate Pulse Width V_{GS} D = Gate Pulse Period 10V (Driver) I_{FM}, Body Diode Forward Current I _{SD} di/dt (DUT) I_{RM} Body Diode Reverse Current V_{DS} (DUT) Body Diode Recovery dv/dt V_{SD} V_{DD} Body Diode Forward Voltage Drop Figure 17. Peak Diode Recovery dv/dt Test Circuit & Waveforms

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